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TABLE OF CONTENTS

Monday - May 11, 2015

9:00 – 10:20

Session 1 – Plenary I

Chairs: Kuang Sheng, *Zhejiang University*
Phil Mawby, *University of Warwick*

9:00

GaN Transistors – Giving New Life to Moore's Law 1
Alex Lidow, *Efficient Power Conversion Corporation*

9:40

Application of Power Electronic Devices in Rail Transportation Traction System 7
Jiaxi Hu, Wenye Liu, Jinfeng Yang, *CSR Zhuzhou Institute Co. Ltd.*

10:50 – 12:10

Session 2 – Plenary II

Chairs: Wai Tung Ng, *University of Toronto*
Kevin Chen, *Hong Kong University of Science and Technology*

10:50

Expansion of LED Lighting and Expectations for Power Semiconductors 13
Shohei Yamamoto, *Eco Solutions Company, Panasonic Corporation*

11:30

How Power Electronics Will Reshape to Meet the 21st Century Challenges? 17
Pierric Gueguen, *Yole Développement*

13:40 – 15:20

Session 3 – High Voltage I

Chairs: Tadahara Minato, *Mitsubishi Electric*
Ali Salih, *ON Semiconductor*

13:40

**Experimental Demonstration of the P-Ring FS+ Trench IGBT Concept:
A New Design for Minimizing the Conduction Losses** 21
M. Antoniou, N. Lophitis, F. Udrea, *University of Cambridge*;
F. Bauer, I. Nistor, M. Bellini, M. Rahimo, *ABB Switzerland Ltd.*

14:05

Ultra Low Miller Capacitance Trench-Gate IGBT with the Split Gate Structure 25
K. Ohi, Y. Ikura, A. Yoshimoto, K. Sugimura, Y. Onozawa, H. Takahashi, M. Otsuki, *Fuji Electric Co., Ltd.*

14:30

- Next Generation 650V CSTBT™ with Improved SOA Fabricated by an Advanced Thin Wafer Technology** 29
Ryu Kamibaba, Kazuya Konishi, Yusuke Fukada, Atsushi Narazaki, Masayoshi Tarutani, *Mitsubishi Electric Corp.*

14:55

- Next Generation 1200V Trench CIGBT for High Voltage Applications** 33
Hong Yao Long, Mark R. Sweet, *University of Sheffield*; Maria Merlyne De Souza, Shankar Narayanan E. Madathil, *University of Sheffield / ECO semiconductors Ltd*

15:50 – 17:05

Session 4 – Wide Bandgap I - GaN I

Chairs: Kevin Chen, *Hong Kong University of Science and Technology*
Yasuhiro Uemoto, *Panasonic*

15:50

- On the Impact of Carbon-Doping on the Dynamic Ron and Off-State Leakage Current of 650V GaN Power Devices** 37
P. Moens, P. Vanmeerbeek, A. Banerjee, J. Guo, C. Liu, P. Coppens, A. Salih, M. Tack, *ON Semiconductor*;
M. Caesar, M.J. Uren, M. Kuball, *Univ. of Bristol*; M. Meneghini, G. Meneghesso, E. Zanoni, *Univ. di Padova*

16:15

- Current-Collapse-Free Operations up to 850 V by GaN-GIT Utilizing Hole Injection from Drain** 41
Saichiro Kaneko, Masayuki Kuroda, Manabu Yanagihara, Ayanori Ikoshi, Hideyuki Okita, Tatsuo Morita, Kenichiro Tanaka, Masahiro Hikita, Yasuhiro Uemoto, Satoru Takahashi, Tetsuzo Ueda, *Panasonic Corporation*

16:40

- Integrated Reverse-Diodes for GaN-HEMT Structures** 45
Richard Reiner, Patrick Waltereit, Beatrix Weiss, Matthias Wespel, Rüdiger Quay, Michael Schlechtweg, Michael Mikulla, Oliver Ambacher, *Fraunhofer-Gesellschaft zur Förderung der angewandten Forschung e. V.*

Tuesday - May 12, 2015

8:30 – 10:10

Session 5 – Integrated Power I

Chairs: Olivier Trescases, *University of Toronto*
YC Jong, *TSMC*

8:30

- A High Current Density SOI-LIGBT with Segmented Trenches in the Anode Region for Suppressing Negative Differential Resistance Regime** 49
Long Zhang, Jing Zhu, Weifeng Sun, Yicheng Du, Hui Yu, Keqin Huang, Longxing Shi, *Southeast University*

8:55

- A Low Substrate Loss, Monolithically Integrated Power Inductor for Compact LED Drivers** 53
Xiangming Fang, Tsz Him Mak, Yuan Gao, Kei May Lau, Philip K.T. Mok, Johnny K.O. Sin, *Hong Kong University of Science and Technology*

9:20

- A Breakthrough Concept of HVICs for High Negative Surge Immunity** 57
Akihiro Jonishi, Masashi Akahane, Masaharu Yamaji, Hiroshi Kanno, Takahide Tanaka, Noriyuki Tochinali, Hitoshi Sumida, *Fuji Electric Co., Ltd.*

9:45

A RESURF P-N Bimodal LDMOS Suitable for High Voltage Power Switching Applications 61
Yongxi Zhang, Sameer Pendharkar, Phil Hower, Salvatore Giombanco, Antonio Amoroso,
Filippo Marino, *Texas Instruments Inc.*

10:40 – 11:55

Session 6 – Low Voltage I

Chairs: Ritu Sodhi, *Empower Semiconductor*
Naoto Fujishima, *Fuji Electric*

10:40

95% DC-DC Conversion Efficiency by Novel Trench Power MOSFET with Dual Channel Structure to Cut Body Diode Losses 65
O. Häberlen, M. Pölzl, J. Schoiswohl, M. Rösch, S. Leomant, G. Nöbauer, W. Rieger,
Infineon Technologies Austria AG

11:05

Investigation of HCI Reliability in Interdigitated LDMOS 69
Kyuheon Cho, Seonghoon Ko, Fumie Machida, Jaeho Kim, Jaejune Jang, Uihui Kwon, Keun-Ho Lee,
Youngkwan Park, *Samsung Electronics Co. Ltd.*

11:30

Optimization of a High-Voltage MOSFET in Ultra-Thin 14nm FDSOI Technology 73
A. Litty, S. Ortolland, D. Golanski, *STMicroelectronics*; S. Cristoloveanu, *IMEP-LAHC*

13:30 – 15:10

Session 7 – Wide Bandgap II - SiC I

Chairs: Lin Cheng, *Texas Tech University*
Noriyuki Iwamuro, *University of Tsukuba*

13:30

Current Enhancement by Conductivity Modulation in Diamond JFETs for Next Generation Low-Loss Power Devices 77
T. Iwasaki, M. Hatano, *Tokyo Institute of Technology / JST-ALCA / JST-CREST*; H. Kato, T. Makino,
M. Ogura, D. Takeuchi, H. Okushi, S. Yamasaki, *JST-CREST / National Institute of Advanced Industrial Science and Technology*; J. Yaita, *Tokyo Institute of Technology*

13:55

Novel Trench-Etched Double-Diffused SiC MOS (TED MOS) for Overcoming Tradeoff Between $R_{on}A$ and Q_{gd} 81
Naoki Tega, Hiroyuki Yoshimoto, Digh Hisamoto, Naoki Watanabe, Haruka Shimizu, Shintaro Sato,
Yuki Mori, Takashi Ishigaki, Mieko Matsumura, Kumiko Konishi, Keisuke Kobayashi, Toshiyuki Mine,
Satoru Akiyama, Ryusei Fujita, Akio Shima, Yasuhiro Shimamoto, *Hitachi, Ltd.*

14:20

The Optimised Design and Characterization of 1200 V / 2.0 mΩ cm² 4H-SiC V-Groove Trench MOSFETs 85
Kosuke Uchida, Yu Saitoh, Toru Hiyoshi, Takeyoshi Masuda, Keiji Wada, Hideto Tamaso, Tomoaki Hatayama,
Kenji Hiratsuka, Takashi Tsuno, Masaki Furumai, Yasuki Mikamura, *Sumitomo Electric Industries, Ltd.*

14:45

Latest Results on 1200 V 4H-SiC CIMOSFETs with $R_{sp,on}$ of 3.9 mΩ·cm² at 150°C (LATE NEWS) 89
Qingchun Zhang, Gangyao Wang, Huy Doan, Sei-Hyung Ryu, Brett Hull,
Jonathan Young, Scott Allen, John Palmour, *Cree, Inc.*

15:10 – 17:00

Poster Session – High Voltage

Temperature Dependence of Single-Event Burnout for Super Junction MOSFET	93
Shunsuke Katoh, Eiji Shimada, Takayuki Yoshihira, Akihiro Oyama, Syotaro Ono, Hideyuki Ura, Gentaro Ookura, Wataru Saito, Yusuke Kawaguchi, <i>Toshiba Corporation</i>	
Predictive Half-Cell Simulations of Filament Formation during IGBT Turn-Off	97
C. Sandow, R. Baburske, V. van Treek, F.-J. Niedernostheide, H.-P. Felsl, M. Cotorogea, <i>Infineon Technologies AG</i>	
Compact Modeling and Analysis of the Partially-Narrow-Mesa IGBT Featuring Low On-Resistance and Low Switching Loss	101
Yosuke Miyaoku, Kai Matsuura, Atsushi Saito, Hideyuki Kikuchihara, Hans Jürgen Mattausch, Mitiko Miura-Mattausch, <i>Hiroshima University</i> ; Daisaku Ikoma, Takao Yamamoto, <i>DENSO Corporation</i>	
Multi-Dimensional Trade-Off Considerations of the 750V Micro Pattern Trench IGBT for Electric Drive Train Applications	105
Frank Wolter, Wolfgang Roesner, Maria Cotorogea, Thomas Geinzer, Martina Seider-Schmidt, <i>Infineon Technologies AG</i> ; Kae-Horng Wang, <i>Infineon Technologies Austria AG</i>	
An Experimental Demonstration of a 4.5 kV “Bi-Mode Gate Commutated Thyristor” (BGCT)	109
Umamaheswara Vemulapati, Martin Arnold, Munaf Rahimo, Jan Vobecky, Thomas Stiasny, <i>ABB Switzerland Ltd.</i> ; Neophytos Lophitis, Florin Udrea, <i>University of Cambridge</i>	
Critical Overcurrent Turn-Off Close to IGBT Current Saturation	113
A. Philippou, C. Jaeger, J.G. Laven, R. Baburske, H.-J. Schulze, F. Pfirsch, F.-J. Niedernostheide, <i>Infineon Technologies AG</i> ; A. Vellei, H. Itani, <i>Infineon Technologies Austria AG</i>	
Investigation of Anode-Side Temperature Effect in 1200V FWD Cosmic Ray Failure	117
Kaname Mitsuzuka, Shoji Yamada, Shunji Takenoiri, Masahito Otsuki, <i>Fuji Electric Co., Ltd.</i> ; Akio Nakagawa, <i>Nakagawa Consulting Office, LLC</i> .	
Simulation Studies for Avalanche Induced Short-Circuit Current Crowding of MOSFET-Mode IGBT	121
Masahiro Tanaka, <i>Nihon Synopsys G.K.</i> ; Akio Nakagawa, <i>Nakagawa Consulting Office, LLC</i> .	
Theoretical Limits of Superjunction Considering with Charge Imbalance Margin	125
Wataru Saito, <i>Toshiba Corporation</i>	
Study about Si Wafer (Mother) Material for High Speed LPT-CSTBT™ based on Electrical and Physical Analysis	129
Kazutoyo Takano, <i>Melco Semiconductor Engineering Corporation</i> ; Akira Kiyoi, Tadaharu Minato, <i>Mitsubishi Electric Corporation</i>	
60 GHz Wireless Signal Transmitting Gate Driver for IGBT	133
Ken-Ichi Yamamoto, Fumio Ichihara, Kazunori Hasegawa, Ichiro Omura, <i>Kyushu Institute of Technology</i> ; Masanori Tukuda, <i>Asian Growth Research Institute</i>	
Superjunction IGBT vs. FS IGBT for 200°C Operation	137
Alice Pei-Shan Hsieh, Gianluca Camuso, Florin Udrea, <i>University of Cambridge</i> ; Chiu Ng, Yi Tang, Rajeev Krishna Vytla, Niraj Ranjan, Alain Charles, <i>International Rectifier Corporation</i>	

15:10 – 17:00

Poster Session – Low Voltage

100 V Class Multiple Stepped Oxide Field Plate Trench MOSFET (MSO-FP-MOSFET) Aimed to Ultimate Structure Realization	141
Kenya Kobayashi, Toshifumi Nishiguchi, Shunsuke Katoh, Takahiro Kawano, Yusuke Kawaguchi, <i>Toshiba Corp.</i>	

Fully-Isolated NLD MOS Behavior Investigation during Reverse Recovery of Parasitic Diodes	145
Nan Ying Yang, Ming Cheng Lin, Haw Yun Wu, C.B. Wu, L. Chu, H.T. Lu, C.Y. Lee, Y.C. Jong, J.L. Tsai, H.C. Tuan, Alex Kalnitsky, <i>Taiwan Semiconductor Manufacturing Company, Ltd.</i>	
A Proposal of LDMOS using Deep Trench Poly Field Plate	149
Joowon Park, Kwangsik Ko, Jina Eum, Kuemju LeeJungsu Jin, Yeounsoo Kim, Seonghoe Jeong, Sanghyun Lee, Jaehye Lee, Inwook Cho, <i>SK Hynix Inc.</i>	
Modeling Spatial and Energy Oxide Trap Distribution Responsible for NBTI in p-Channel Power U-MOSFETs	153
Andrea N. Tallarico, Enrico Sangiorgi, Claudio Fiegna, <i>Università di Bologna</i> ; Paolo Magnone, <i>University of Padova</i> ; Giacomo Barletta, Angelo Magri, <i>STMicroelectronics</i>	
A Vertical Current Regulator Diode with Trench Cathode based on Double Epitaxial Layers for LED Lighting	157
Yitao He, Ming Qiao, Gang Dai, Liangliang Yu, Kang Zhang, Zhaoji Li, Yunyang Tang, Bo Zhang, <i>University of Electronic Science and Technology of China</i> ; Xin Zhao, Jianfeng Ou, <i>Chip Hope Micro-electronics Co., Ltd.</i> ; Xuqiang Zhu, <i>Dongguang Micro-electronics Co., Ltd.</i>	
Hot-Carrier Injection Effect in SOI SJ-LDMOS	N/A
Chao Xia, Xinhong Cheng, Zhongjian Wang, Dawei Xu, Duo Cao, Li Zheng, Lingyang Shen, Qian Wang, Yuehui Yu, <i>Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences</i>	
15:10 – 17:00	
Poster Session – Integrated Power	
The Boost Transistor: a Field Plate Controlled LDMOST	165
A. Ferrara, B.K. Boksteen, J. Schmitz, R.J.E. Hueting, <i>University of Twente</i> ; A. Heringa, J. Claes, A. van der Wel, <i>NXP Semiconductors</i> ; P.G. Steeneken, <i>NXP Semiconductors / Technische Universiteit Delft</i>	
High Voltage Thick SOI-LIGBT with High Current Density and Latch-Up Immunity	169
Jing Zhu, Weifeng Sun, Long Zhang, Yicheng Du, Hui Yu, Keqin Huang, <i>Southeast University</i> ; Yan Gu, Sen Zhang, Wei Su, <i>CSMC Technologies Corporation</i>	
A Capacitive-Loaded Level Shift Circuit for Improving the Noise Immunity of High Voltage Gate Drive IC	173
Yunwu Zhang, Jing Zhu, Weifeng Sun, Yangyang Lu, <i>Southeast University</i> ; Lihui Gu, Sen Zhang, Wei Su, <i>CSMC Technologies Corporation</i>	
A 0.18µm SOI BCD Technology for Automotive Application	177
Y. Hao, P.C. Sim, B. Toner, A. Tan, E. Kho, E.G. Hee, M. Liew, A. Hoelke, <i>X-FAB Sarawak Sdn. Bhd.</i> ; M. Frank, M. Ackermann, U. Kuniss, J. Doblaski, <i>X-FAB Semiconductor Foundries AG</i> ; S. Wada, <i>Hitachi, Ltd.</i> ; T. Oshima, <i>Hitachi Automotive Systems</i>	
The Effect of the Collector Contact Design on the Performance and Yield of 800V Lateral IGBTs for Power ICs	181
G. Camuso, F. Udrea, <i>University of Cambridge</i> ; N. Udugampola, V. Pathirana, T. Trajkovic, F. Udrea, <i>Cambridge Microelectronics Ltd</i>	
Accumulation-Mode High Voltage SOI LDMOS with Ultralow Specific On-Resistance	185
Jie Wei, Xiaorong Luo, Yanhui Zhang, Pengcheng Li, Kun Zhou, Zhaoji Li, Dameng Lei, Fanzhou He, Bo Zhang, <i>University of Electronic Science and Technology of China</i>	
Automatic Layout Optimization of DMOS Transistors for Lower Peak Temperatures and Increased Energy Capability	189
Timo Zawischka, Martin Pfof, <i>Hochschule Reutlingen</i>	

Demonstration of a HV BCD Technology with LV CMOS Process	193
Tsung-Yi Huang, Ching-Yao Yang, Huang-Ping Chu, Chien-Wei Chiu, Hung-Der Su, Jing-Meng Liu, <i>Richtek Technology Corporation</i> ; Chien-Hao Huang, Kuo-Hsuan Lo, <i>Richtek Technology Corporation / National Tsing Hua University</i> ; Chih-Fang Huang, <i>National Tsing Hua University</i> ; Wang-Chi Vincent Yeh, <i>National Dong Hwa University</i> ; Jeng Gong, <i>Tunghai University</i>	
15:10 – 17:00	
Poster Session – Wide Bandgap	
4 A/cm², 7kV Normally-Off Diamond-Emitter Vacuum Switch	197
D. Takeuchi, H. Kawashima, D. Kuwabara, T. Makino, H. Kato, M. Ogura, H. Ohashi, H. Okushi, S. Yamasaki, S. Koizumi, <i>National Institute of Advanced Industrial Science and Technology</i>	
On-Chip Optical Pumping of Deep Traps in AlGaIn/GaN-on-Si Power HEMTs	201
Xi Tang, Baikui Li, Kevin J. Chen, <i>Hong Kong University of Science and Technology</i>	
Investigations on Degradation and Optimization of 1.2kV 4H-SiC MOSFET Under Repetitive Unclamped Inductive Switching Stress	205
Siyang Liu, Weifeng Sun, Qinsong Qian, Chunde Gu, Yu Huang, <i>Southeast University</i> ; Song Bai, Gang Chen, Runhua Huang, Yonghong Tao, Ao Liu, <i>CETC (Nanjing) Electronics Information Development Co., Ltd</i>	
Enhancement-Mode GaN-on-Si MOS-FET using Au-Free Si Process and its Operation in PFC System with High-Efficiency	209
Hironobu Miyamoto, Yasuhiro Okamoto, Hiroshi Kawaguchi, Tatsuo Nakayama, Ichiro Masumoto, Shinichi Miyake, Tomohiro Hirai, Machiko Fujita, Takehiro Ueda, Katsumi Yamanoguchi, Atsushi Tsuboi, <i>Renesas Semiconductor Manufacturing Co., Ltd.</i> ; Yoshinao Miura, <i>Renesas System Design Co., Ltd.</i> ; Makoto Nakamura, <i>Renesas Electronics Co., Ltd.</i>	
Normally-Off GaN MIS-HEMT with Improved Thermal Stability in DC and Dynamic Performance	213
Cheng Liu, Hanxing Wang, Shu Yang, Yunyou Lu, Shenghou Liu, Zhikai Tang, Qimeng Jiang, Kevin J. Chen, <i>Hong Kong University of Science and Technology</i> ; Sen Huang, <i>Chinese Academy of Sciences</i>	
Electro-Thermal Simulation of 1200 V 4H-SiC MOSFET Short-Circuit SOA	217
T.H. Duong, J.M. Ortiz, D.W. Berning, A.R. Hefner, <i>National Institute of Standards and Technology</i> ; S.-H. Ryu, J.W. Palmour, <i>Cree, Inc.</i>	
Series-Connection of SiC Normally-On JFETs	221
Xueqing Li, Anup Bhalla, Petre Alexandrov, John Hostetler, Leonid Fursin, <i>United Silicon Carbide, Inc.</i>	
The Impact of the Gate Dielectric Quality in Developing Au-Free D-Mode and E-Mode Recessed Gate AlGaIn/GaN Transistors on a 200mm Si Substrate	225
Tian-Li Wu, Guido Groeseneken, <i>IMEC / Katholieke Universiteit Leuven</i> ; Denis Marcon, Brice De Jaeger, Marleen Van Hove, Dennis Lin, Steve Stoffels, Xuanwu Kang, Stefaan Decoutere, <i>IMEC</i> ; Benoit Bakeroort, <i>IMEC / Ghent University</i> ; Robin Roelofs, <i>ASM International N.V.</i>	
Static and Dynamic Performance Characterization and Comparison of 15 kV SiC MOSFET and 15 kV SiC n-IGBTs	229
Gangyao Wang, <i>North Carolina State University / Cree Inc.</i> ; Alex Q. Huang, Fei Wang, Xiaoqing Song, Xijun Ni, <i>North Carolina State University</i> ; Sei-Hyung Ryu, David Grider, Marcelo Schupbach, John Palmour, <i>Cree, Inc.</i>	
Enhancement-Mode GaN-on-Silicon MOS-HEMT using Pure Wet Etch Technique	233
Cen Tang, Gang Xie, Kuang Sheng, <i>Zhejiang University</i>	
70 mΩ / 600 V Normally-Off GaN Transistors on SiC and Si Substrates	237
Oliver Hilt, Rimma Zhytnytska, Eldad Bahat-Treidel, Frank Brunner, Arne Knauer, Joachim Würfl, <i>Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik</i> ; Jan Böcker, Sibylle Dieckerhoff, <i>Technische Universität Berlin</i>	

650-V GaN-Based MIS-HEMTs using LPCVD-SiN_x as Passivation and Gate Dielectric	241
Mengyuan Hua, Cheng Liu, Shu Yang, Shenghou Liu, Yunyou Lu, Kevin J. Chen, <i>Hong Kong University of Science and Technology</i> ; Kai Fu, Zhihua Dong, Yong Cai, Baoshun Zhang, <i>Suzhou Institute of Nano-Tech and Nano-Bionics, Chinese Academy of Science</i>	
Stability of Silicon Carbide Schottky Diodes against Leakage Current Thermal Runaway	245
Christian Bödeker, Timo Vogt, Nando Kaminski, <i>Universität Bremen</i>	
Area- and Efficiency-Optimized Junction Termination for a 5.6 kV SiC BJT Process with Low On-Resistance	249
Arash Salemi, Hossein Elahipanah, Gunnar Malm, Carl-Mikael Zetterling, Mikael Östling, <i>KTH Royal Institute of Technology</i>	
High-Voltage Full-SiC Power Module: Device Fabrication, Testing and High Frequency Application in kW-Level Converter	253
Sizhe Chen, Junwei He, Kuang Sheng, <i>Zhejiang University</i>	
The First Demonstration of Symmetric Blocking SiC Gate Turn-Off (GTO) Thyristor	257
Woongje Sung, Alex Q. Huang, B.J. Baliga, Inhwan Ji, Haotao Ke, Douglas C. Hopkins, <i>North Carolina State Univ.</i>	
Influence of Epitaxy and Gate Deposition Process on Ron Resistance of AlGaIn/GaN-on-Si HEMT	261
J. Lehmann, <i>CEA-LETI / IMEP-LAHC</i> ; C. Leroux, M. Charles, A. Torres, E. Morvan, G. Reimbold, <i>CEA-LETI</i> ; E. Bano, G. Ghibaudo, <i>IMEP-LAHC</i>	
1700V/30A 4H-SiC MOSFET with Low Cut-In Voltage Embedded Diode and Room Temperature Boron Implanted Termination	265
Cheng-Tyng Yen, Chien-Chung Hung, Hsiang-Ting Hung, Lurng-Shehng Lee, Chwan-Ying Lee, Tzu-Ming Yang, Yao-Feng Huang, Chi-Yin Cheng, Pei-Ju Chuang, <i>Hestia Power Incorporation</i>	
Conductivity Modulated On-Axis 4H-SiC 10+ kV Pin Diodes	269
Arash Salemi, Hossein Elahipanah, Anders Hallén, Gunnar Malm, Carl-Mikael Zetterling, Mikael Östling, <i>KTH Royal Institute of Technology</i> ; Benedetto Buono, <i>Fairchild Semiconductor</i> ; Jawad Ul Hassan, Peder Bergman, <i>Linköping University</i>	
Design and Optimization of GaN Lateral Polarization-Doped Super-Junction (LPSJ): An Analytical Study	273
Bo Song, Debdeep Jena, Huili Grace Xing, <i>Cornell University / University of Notre Dame</i> ; Mingda Zhu, Zongyang Hu, Kazuki Nomoto, <i>University of Notre Dame</i>	
22 kV SiC Emitter Turn-Off (ETO) Thyristor and Its Dynamic Performance Including SOA	277
Xiaoqing Song, Alex Q. Huang, Meng-Chia Lee, Chang Peng, <i>North Carolina State University</i> ; Lin Cheng, <i>North Carolina State University / U.S. Army Research Laboratory</i> ; Heather O'Brien, Aderin Oggunniyi, Charles Scozzie, <i>U.S. Army Research Laboratory</i> ; John Palmour, <i>Cree, Inc.</i>	
Development of Power Semiconductors by Quantitative Nanoscale Dopant Imaging	281
H. Bartolf, <i>ABB Switzerland Ltd.</i> ; U. Gysin, <i>University of Basel</i> ; H.R. Rossmann, T.A. Jung, <i>University of Basel / Paul Scherrer Institute</i> ; A. Bubendorf, T. Glatzel, E. Meyer, <i>University of Basel</i> ; M. Zimmermann, <i>Institut für Mikroelektronik Stuttgart</i> ; S. Reshanov, A. Schöner, <i>Ascatron AB</i>	
A Monolithic SiC Drive Circuit for SiC Power BJTs	285
Saleh Kargarrazi, Luigia Lanni, Ana Rusu, Carl-Mikael Zetterling, <i>KTH Royal Institute of Technology</i>	
High Voltage Si/SiC Hybrid Switch: An Ideal Next Step for SiC	289
Xiaoqing Song, Alex Q. Huang, Meng-Chia Lee, Chang Peng, <i>North Carolina State University</i>	
SiC Reversely Switched Dynistor (RSD) for Pulse Power Application	293
Lin Liang, Cheng Liu, Wenguang Chang, <i>Huazhong University of Science & Technology</i> ; Alex Q. Huang, <i>North Carolina State University</i>	

15:10 – 17:00

Poster Session – Packaging

A Novel 3D Transformer for Ultra-Compact Signal Isolation	297
Rongxiang Wu, Niteng Liao, <i>University of Electronic Science and Technology of China</i> ; Xiangming Fang, Johnny K.O. Sin, <i>Hong Kong University of Science and Technology</i>	
Accelerated Resistance Degradation in Aluminum by Pulsed Power Cycling	301
A. Ferrara, <i>University of Twente</i> ; J. Claes, Swanenberg, L. van Dijk, <i>NXP Semiconductors</i> ; P.G. Steeneken, <i>NXP Semiconductors / Technische Universiteit Delft</i>	
Optimization of HV LDMOS Devices Accounting for Packaging Interaction	305
G. Arienti, I. Imperiale, S. Reggiani, E. Gnani, A. Gnudi, G. Baccarani, <i>Università di Bologna</i> ; L. Nguyen, A. Hernandez-Luna, J. Huckabee, M. Denison, <i>Texas Instruments Inc.</i>	
Reduced Active and Passive Thermal Cycling Degradation by Dynamic Active Cooling of Power Modules	309
Xiang Wang, Yun Wang, Alberto Castellazzi, <i>University of Nottingham</i>	
Ultra Low Inductance Power Module for Fast Switching SiC Power Devices	313
Kazuto Takao, Shinya Kyogoku, <i>Toshiba Corporation</i>	

Wednesday - May 13, 2015

9:00 – 10:40

Session 8 – Packaging I

Chairs: Kimimori Hamada, *Toyota Motor*
Katsuaki Saito, *Hitachi*

9:00

Trends and Opportunities in Intelligent Power Modules (IPM) – INVITED	317
Masahito Otsuki, Manabu Watanabe, Akira Nishiura, <i>Fuji Electric Co., Ltd.</i>	

9:25

Lifetime Analysis of Power Modules with New Packaging Technologies	321
N. Heuck, R. Bayerer, S. Krasel, F. Otto, R. Speckels, K. Guth, <i>Infineon Technologies AG</i>	

9:50

Methods for Virtual Junction Temperature Measurement Respecting Internal Semiconductor Processes	325
Christian Herold, Jörg Franke, Riteshkumar Bhojani, Andre Schleicher, Josef Lutz, <i>Technische Universität Chemnitz</i>	

10:15

Highly Integrated Low-Inductive Power Switches using Double-Etched Substrates with Through-Hole Viases	329
Adane Kassa Solomon, Alberto Castellazzi, <i>University of Nottingham</i> ; Nicola Delmonte, Paolo Cova, <i>Università degli Studi di Parma</i>	

11:10 – 12:25

Session 9 – Integrated Power II

Chairs: Alex Hoelke, *XFAB*

Jun Cai, *Texas Instruments*

11:10

Fully Integrated SOI Gate Driver for Control of 1200V IGBT Switches in Three-Level-NPC Topology 333

Bastian Vogler, Reinhard Herzer, Sven Buetow, *Semikron*

11:35

Fully-Isolated Silicon RF LDMOS for High-Efficiency Mobile Power Conversion and RF Amplification 337

Michael Zierak, Natalie Feilchenfeld, Chaojiang Li, Ted Letavic, *International Business Machines Corporation*

12:00

Substrate Coupling in Fast-Switching Integrated Power Stages 341

Juergen Wittmann, Christoph Rindfleisch, Bernhard Wicht, *Hochschule Reutlingen*

14:00 – 15:15

Session 10 – Wide Bandgap III - SiC II

Chairs: Peter Losse, *GE*

Kung-Yen Lee, *National Taiwan University*

14:00

Short-Circuit Failure Mechanism of SiC Power MOSFETs 345

G. Romano, L. Maresca, M. Riccio, V. D'Alessandro, G. Breglio, A. Irace, *Università degli Studi di Napoli Federico II*; A. Fayyaz, A. Castellazzi, *University of Nottingham*

14:25

A 10kV/200A SiC MOSFET Module with Series-Parallel Hybrid Connection of 1200V/50A Dies 349

Qiang Xiao, Yang Yan, Xinke Wu, Na Ren, Kuang Sheng, *Zhejiang University*

14:50

Characteristics of 4H-SiC P-i-N Diodes on Lightly Doped Free-Standing Substrates 353

S. Chowdhury, C. Hitchcock, R. Dahal, I.B. Bhat, T.P. Chow, *Rensselaer Polytechnic Institute*

15:45 – 17:50

Session 11 – Wide Bandgap IV - GaN II

Chairs: Oliver Haeberlen, *Infineon Technologies*

Chih-Fang Huang, *National Tsing Hua University*

15:45

GaN-Based Monolithic Power Integrated Circuit Technology with Wide Operating Temperature on Polarization-Junction Platform 357

Akira Nakajima, Shin-Ichi Nishizawa, Hiromichi Ohashi, *National Institute of Advanced Industrial Science and Technology*; Rei Kayanuma, Kazuo Tsutsui, Shunsuke Kubota, Kuniyuki Kakushima, Hitoshi Wakabayashi, Hiroshi Iwai, *Tokyo Institute of Technology*

16:10

A GaN HEMT Driver IC with Programmable Slew Rate and Monolithic Negative Gate-Drive Supply and Digital Current-Mode Control 361

M. Rose, R. Van Otten, H.J. Bergveld, *NXP Semiconductors*;

Y. Wen, R. Fernandes, O. Trescases, *University of Toronto*

16:35

Impact of the Backside Potential on the Current Collapse of GaN SBDs and HEMTs 365

J.A. Croon, G.A.M. Hurkx, J.J.T.M. Donkers, J. Šonský, *NXP Semiconductors*

17:00

Over 1.1 kV Breakdown Low Turn-On Voltage Ga-Non-Si Power Diode with MIS-Gated Hybrid Anode 369

Qi Zhou, Yang Jin, Jingyu Mou, Xu Bao, Yijun Shi, Zhaoyang Liu, Jian Li, Wanjun Chen, Chongwen Sun, Bo Zhang, *University of Electronic Science and Technology of China*

17:25

Quasi-Normally-Off GaN Gate Driver for High Slew-Rate D-Mode GaN-on-Si HEMTs (LATE NEWS) 373

S. Mönch, M. Costa, A. Barner, I. Kallfass, *University of Stuttgart*; R. Reiner, B. Weiss, P. Waltereit, R. Quay, O. Ambacher, *Fraunhofer Institute for Applied Solid State Physics*

Thursday - May 14, 2015

9:00 – 10:15

Session 12 – Packaging II

Chairs: Reinhold Bayerer, *Infineon Technologies*
Alberto Castellazzi, *Nottingham University*

9:00

A Modeling and Experimental Method for Accurate Thermal Analysis of AlGaIn/GaN Powerbars 377

Vice Šodan, Ingrid De Wolf, *IMEC / Katholieke Universiteit Leuven*; Steve Stoffels, Herman Oprins, Stefaan Decoutere, *IMEC*; Martine Baelmans, *Katholieke Universiteit Leuven*

9:25

Numerical Study of GaN-on-Si HEMT Breakdown Instability Accounting for Substrate and Packaging Interactions 381

F. Monti, I. Imperiale, S. Reggiani, E. Gnani, A. Gnudi, G. Baccarani, *Università di Bologna*; L. Nguyen, A. Hernandez-Luna, J. Huckabee, N. Tipirneni, M. Denison, *Texas Instruments Inc.*

9:50

Acceleration of Temperature Humidity Bias (THB) Testing on IGBT Modules by High Bias Levels 385

Christian Zorn, Nando Kaminski, *Universität Bremen*

10:45 – 12:00

Session 13 – Low Voltage II

Chairs: Jun Zeng, *MaxPower Semiconductor*
Yusuke Kawaguchi, *Toshiba*

10:45

Predictive and Efficient Modeling of Hot-Carrier Degradation in nLDMOS Devices 389

Prateek Sharma, *Technische Universität Wien*; Stanislav Tyaginov, *Technische Universität Wien / Ioffe Physical-Technical Institute of the Russian Academy of Sciences*; Yannick Wimmer, Florian Rudolf, Karl Rupp, Markus Bina, Hajdin Ceric, Tibor Grasser, *Technische Universität Wien*; Hubert Enichlmair, Jong-Mun Park, *ams AG*

11:10

An Advanced p-Channel LDMOS FET with HTRB Tolerability of High-Voltage Pulse Transmitter ICs for Ultrasound Applications 393
Tomoyuki Miyoshi, Shinichiro Wada, Toshio Shinomiya, Satoshi Ueno, *Hitachi, Ltd.*

11:35

Self-Heating Enhanced HCI Degradation in pLDMOSFETs 397
Yandong He, Ganggang Zhang, Xing Zhang, *Peking University*

14:00 – 15:40

Session 14 – High Voltage II

Chairs: Shuai Zhang, *TSMC*
Nando Kaminski, *University of Bremen*

14:00

A Novel Trench Shielded MOSFET with Buried Field Ring for Tunable Switching and Improved Ruggedness 401
Lingpeng Guan, Madhur Bobde, Karthik Padmanabhan, Hamza Yilmaz, Lei Zhang, Allan Chiu, Jongoh Kim, Wenjun Li, *Alpha and Omega Semiconductor*; Anup Bhalla, *United Silicon Carbide, Inc.*

14:25

Suppression of Switching Loss Dependence on Charge Imbalance of Superjunction MOSFET 405
Hiroaki Yamashita, Hideyuki Ura, Syotaro Ono, Masato Nashiki, Kenji Mii, Wataru Saito, Jun Onodera, Yoshitaka Hokomoto, *Toshiba Corporation*

14:50

1.7kV High-Power IGBT Fabrication by Bonded-Wafer-Concept 409
Sven Matthias, Wolfgang Janisch, Charalampos Papadopoulos, Arnost Kopta, *ABB Switzerland Ltd.*

15:15

A Novel Ultra-Low Loss Four Inch Thyristor for UHVDC 413
J. Vobecky, V. Botan, K. Stiegler, U. Meier, M. Bellini, *ABB Switzerland Ltd.*